

| L<br>Number | Hits   | Search Text   | DB  | Time stamp          |
|-------------|--------|---|---|---------------------|
| 1           | 504784 | ((semiconductor si silicon gaas p n) with (substrate))  | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:05 |
| 2           | 41054  | ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate)))   | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:05 |
| 3           | 573358 | high with (current power)   | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:05 |
| 4           | 104885 | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)   | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:07 |
| 5           | 10060  | ((semiconductor si silicon gaas p n) with (substrate)) same interconnect  | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:07 |
| 6           | 1197   | ((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power))  | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:08 |
| 7           | 8366   | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes) and ((multiple different plurality) with (metal interconnect))  | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:10 |
| 8           | 78     | ((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power)) and ((multiple different plurality) with (metal interconnect)) | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:17 |
| 9           | 4691   | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes) and ((multiple different plurality) with (metal interconnect)) ) and (diffusion barrier)  | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:19 |
| 10          | 4691   | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes) and ((multiple different plurality) with (metal interconnect)) ) and (diffusion barrier)  | USPAT;<br>US-PGPUB;<br>EPC; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:19 |

| Number | Hits   | Search Text   | DB  | Time stamp          |
|--------|--------|---|---|---------------------|
| 1      | 504784 | ((semiconductor si silicon gaas p n) with (substrate))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:05 |
| 2      | 41054  | ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate)))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:05 |
| 3      | 573358 | high with (current power)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:06 |
| 4      | 104885 | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:07 |
| 5      | 10060  | ((semiconductor si silicon gaas p n) with (substrate)) same interconnect  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:07 |
| 6      | 1197   | ((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:08 |
| 7      | 8366   | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)) and ((multiple different plurality) with (metal interconnect))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:10 |
| 8      | 78     | ((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power)) and ((multiple different plurality) with (metal interconnect)) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:10 |
| 9      | 4691   | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)) and ((multiple different plurality) with (metal interconnect)) ) and (diffusion barrier)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:19 |
| 10     | 4691   | ((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)) and ((multiple different plurality) with (metal interconnect)) ) and (diffusion barrier)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:19 |
| 11     | 262    | ((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power))) and (different with (metal layer interconnect))               | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DEFWENT;<br>IBM_TDB | 2002/09/17<br>14:21 |